

PRODUCT SUMMARY

 $I_{T(AV)}$

110RKI...PbF, 111RKI...PbF Series

Vishay Semiconductors

Phase Control Thyristors (Stud Version), 110 A



110 A

FEAT	JRES
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• High current and high surge ratings



· Hermetic ceramic housing

ROHS

• Designed and qualified for industrial level

 Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
1		110	A	
I _{T(AV)}	T _C	90	°C	
I _{T(RMS)}		172		
	50 Hz	2080	A	
I _{TSM}	60 Hz	2180		
l²t	50 Hz	21.7	1.42-	
1-1	60 Hz	19.8	kA ² s	
V _{DRM} /V _{RRM}		400 to 1200	V	
tq	Typical	110	μѕ	
TJ		- 40 to 140	°C	

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA			
	40	400	500				
110RKI 111RKI	80	800	900	20			
	120	1200	1300				



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ABSOLUTE MAXIMUM RATINGS	S						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS	
Maximum average on-state current	I	180° condu	ction, half sine v	NOVA	110	Α	
at case temperature	I _{T(AV)}	100 Condu	Ction, nan sine v	wave	90	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 83 °C	case temperat	ure	172		
		t = 10 ms	No voltage		2080		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		2180	A kA ² s	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		1750		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1830		
Marian 121 6 1 6 1 6 1 1 1 1		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	21.7		
	l ² t	t = 8.3 ms			19.8		
Maximum I ² t for fusing		1-1	t = 10 ms	100 % V _{RRM}		15.3	KA-S
		t = 8.3 ms	reapplied		14.0		
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		217	kA²√s		
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		0.82	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.02	V		
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		2.16	 0		
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.70	mΩ		
Maximum on-state voltage	V_{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$		1.57	V		
Maximum holding current	I _H			V registive lead	200	A	
Typical latching current	ΙL	T _J = 25 °C, anode supply 6 V resistive load		400	mA		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	300	A/μs	
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1		
Typical turn-off time	t _q	I_{TM} = 50 A, T_J = T_J maximum, dl/dt = - 5 A/ μ s V_R = 50 V, dV/dt = 20 V/ μ s, gate 0 V 25 Ω	110	μs	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs	
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA	

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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PARAMETER	STIVIBUL	1531	CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	12		W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	3	.0	VV
Maximum peak positive gate current	I _{GM}			3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	2	20	
Maximum peak negative gate voltage	- V _{GM}			10		V
		T _J = - 40 °C	Maximum required gate trigger/current/voltage are the lowest value which will	180	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		80	120	mA
		T _J = 140 °C		40	-	
		T _J = - 40 °C	trigger all units 12 V anode	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	to cathode applied	1.6	2	V
		T _J = 140 °C		1	-	
DC gate current not to trigger	I _{GD}	T. T. maximum	Maximum gate current/ voltage not to trigger is the maximum value which will			mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J \text{ maximum}$	not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		- 40 to 140	°C	
Maximum storage temperature range	T _{Stg}		- 40 to 150		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.27	0.27 0.1 K/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.1		
Mounting toyang 1100/		Non-lubricated threads	15.5 (137)	N · m	
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet	TO-209AC	(TO-94)	

△R _{thJC} CONDUCTION					
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS	
180°	0.043	0.031			
120°	0.052	0.053			
90°	0.066	0.071	$T_J = T_J$ maximum	K/W	
60°	0.096	0.101			
30°	0.167	0.169			

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



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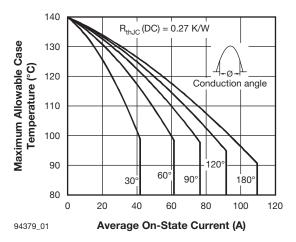


Fig. 1 - Current Ratings Characteristics

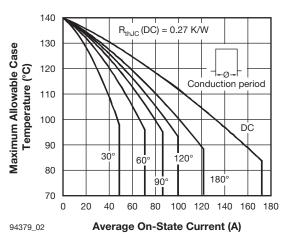
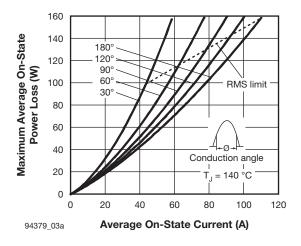


Fig. 2 - Current Ratings Characteristics



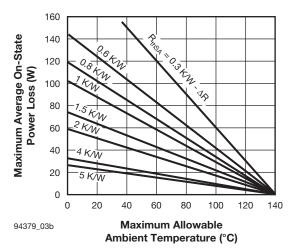
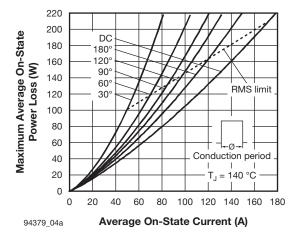


Fig. 3 - On-State Power Loss Characteristics



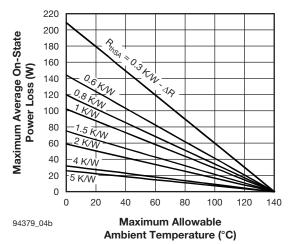


Fig. 4 - On-State Power Loss Characteristics



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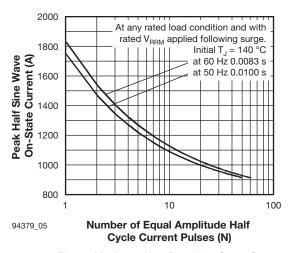


Fig. 5 - Maximum Non-Repetitive Surge Current

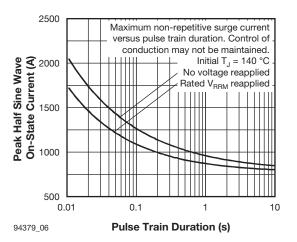


Fig. 6 - Maximum Non-Repetitive Surge Current

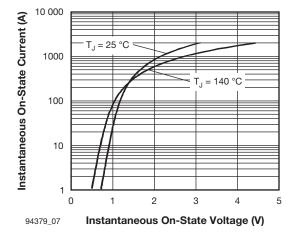


Fig. 7 - On-State Voltage Drop Characteristics

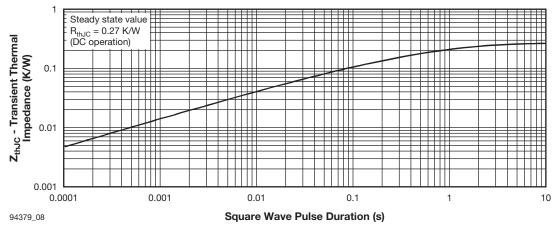


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

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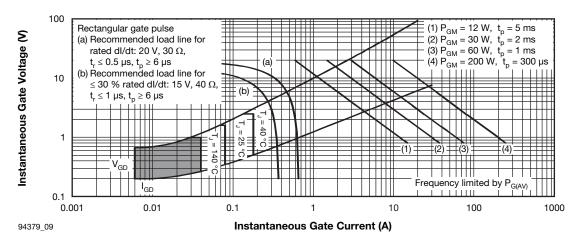
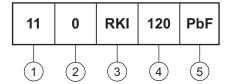


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - I_{T(AV)} rated average output current (rounded/10)

2 - • 0 = Eyelet terminals (gate and auxiliary cathode leads)

• 1 = Fast-on terminals (gate and auxiliary cathode leads)

3 - Thyristor

Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

5 - • None = Standard production

• PbF = Lead (Pb)-free

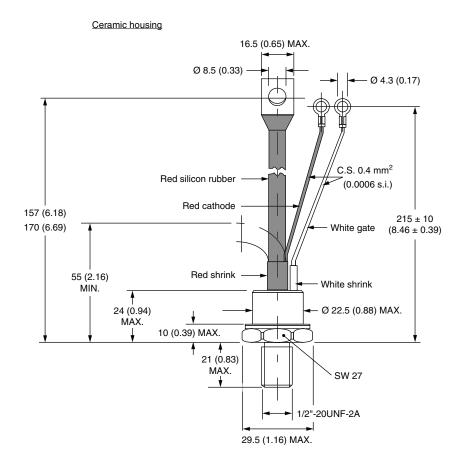
LINKS TO RELAT	
Dimensions	www.vishay.com/doc?95003

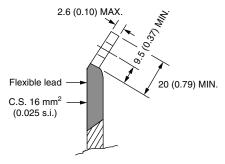


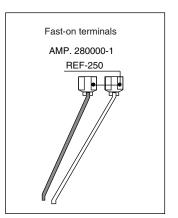
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TO-209AC (TO-94) for 110RKI and 111RKI Series

DIMENSIONS in millimeters (inches)







Note

• For metric device: M12 x 1.75 contact factory



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